

SANYO

No.1801E

2SC3676

NPN Triple Diffused Planar Silicon Transistor

High-Voltage Amp,
High-Voltage Switching Applications**Applications**

- High-voltage amplifiers.
- High-voltage switching applications.
- Dynamic focus applications.

Features

- High breakdown voltage ($V_{CEO \text{ min}} = 900\text{V}$).
- Small Cob (Cob typ = 5.0pF).
- Wide ASO (Adoption of MBIT process).
- High reliability (Adoption of HVP process).

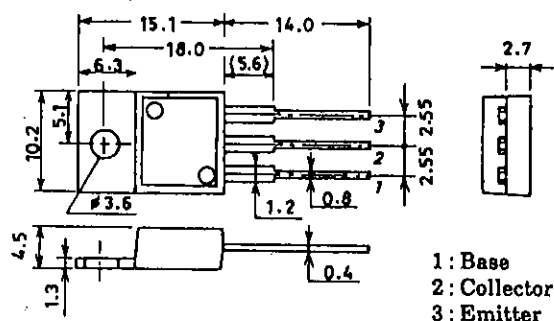
Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

			unit
Collector-to-Base Voltage	V_{CBO}	1500	V
Collector-to-Emitter Voltage	V_{CEO}	900	V
Emitter-to-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	300	mA
Collector Current (Pulse)	I_{CP}	1	A
Collector Dissipation	P_C	20	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

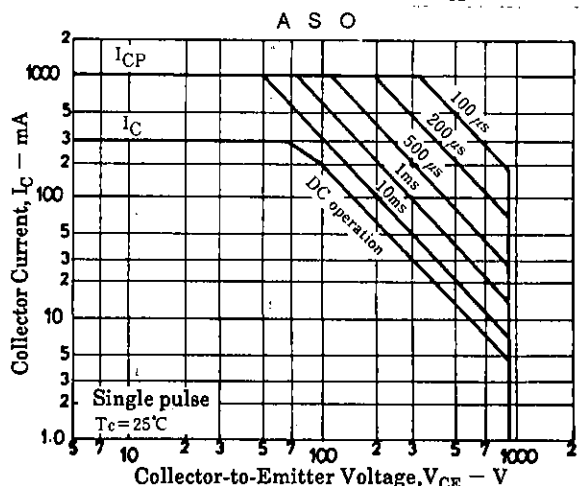
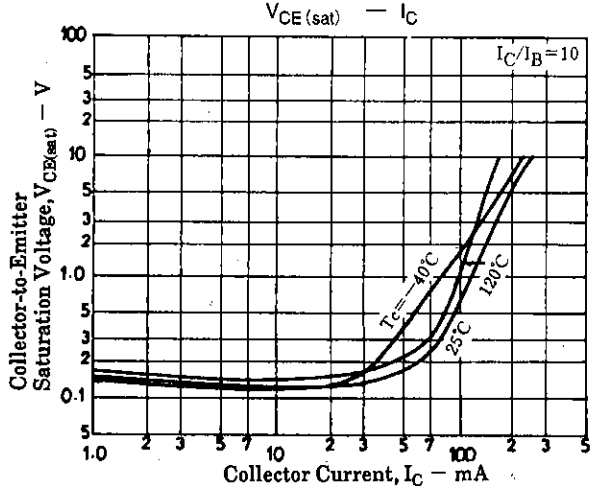
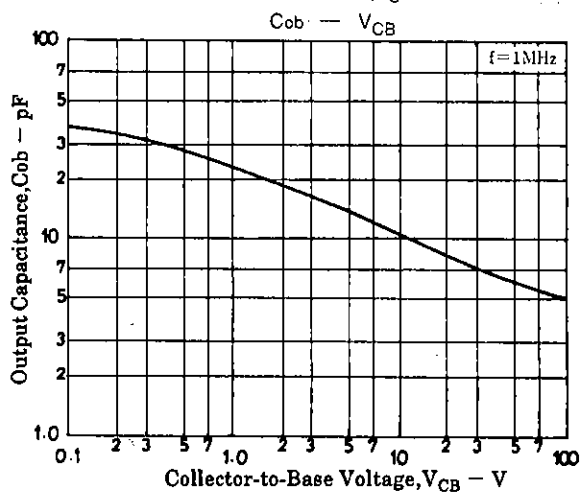
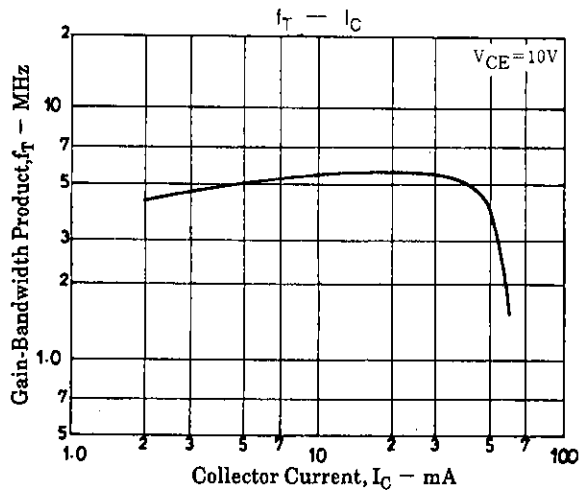
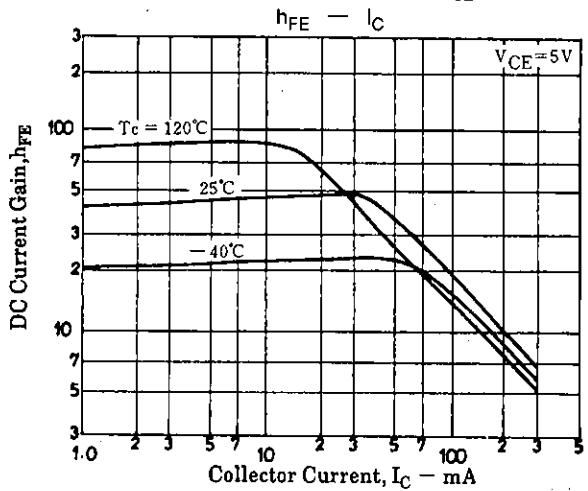
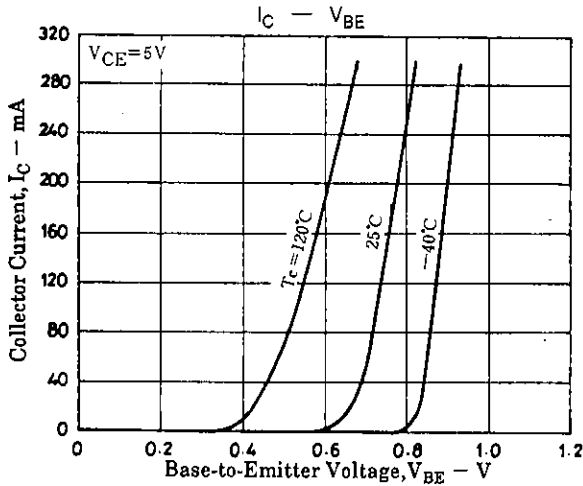
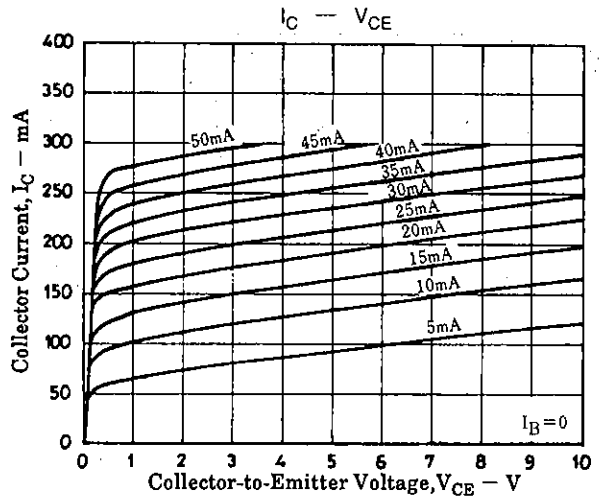
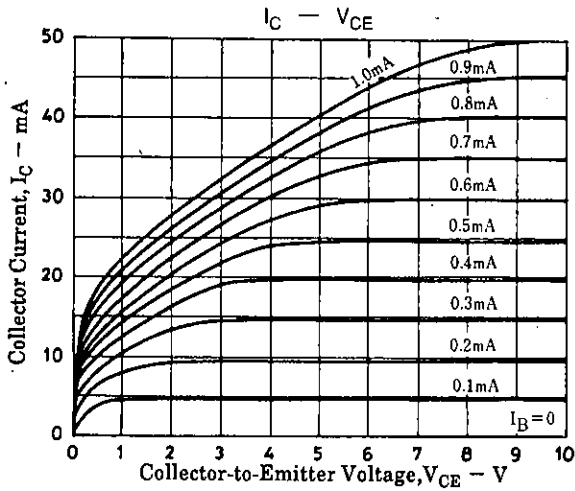
$T_c = 25^\circ\text{C}$

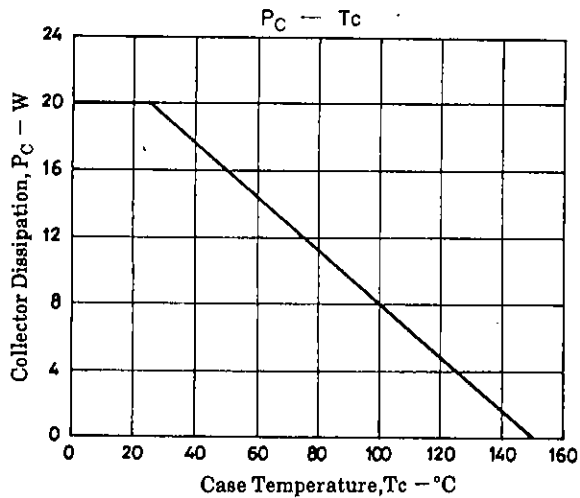
Electrical Characteristics at $T_a = 25^\circ\text{C}$

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 900\text{V}, I_E = 0$			10	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 4\text{V}, I_C = 0$			10	μA
DC Current Gain	h_{FE}	$V_{CE} = 5\text{V}, I_C = 30\text{mA}$	30			
Gain-Bandwidth Product	f_T	$V_{CE} = 10\text{V}, I_C = 30\text{mA}$		6		MHz
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = 60\text{mA}, I_B = 12\text{mA}$			5	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = 60\text{mA}, I_B = 12\text{mA}$			2	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 1\text{mA}, I_E = 0$	1500			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1\text{mA}, R_{BE} = \infty$	900			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 1\text{mA}, I_C = 0$	5			V
Output Capacitance	Cob	$V_{CB} = 100\text{V}, f = 1\text{MHz}$		5.0		pF

Package Dimensions 2010C
(unit: mm)JEDEC: TO220AB
EIAJ: SC46

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